TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

HN2C26FS

Frequency General-Purpose Amplifier Applications

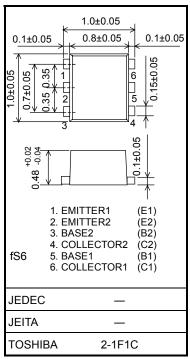
- Two devices are incorporated into a fine-pitch, Small-Mold (6-pin)
 package
- High voltage: V_{CEO} = 50 V
- High current: I_C = 100 mA (max)
- High hFE: hFE = 120 to 400
- Excellent hFE linearity

: $h_{FE} (I_C = 0.1 \text{ mA})/h_{FE} (I_C = 2 \text{ mA}) = 0.95 (typ.)$

Lead (Pb) - free

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	۱ _C	100	mA
Base current	Ι _Β	30	mW
Collector power dissipation	P _C (Note)	50	mW
Junction temperature	Тј	150	°C
Storage temperature range	T _{stg}	-55 ~ 150	°C



Weight: 0.001 g (typ.)

Note: Total rating.

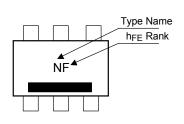
Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cutoff current	I _{CBO}	$V_{CB} = 60 V, I_{E} = 0$	—		0.1	μA
Emitter cutoff current	I _{EBO}	$V_{EB}=5~V,~I_C=0$	_	_	0.1	μA
DC current gain	h _{FE} (Note)	$V_{CE} = 6 V, I_C = 2 mA$	120	_	400	
Collector-emitter saturation voltage	V _{CE (sat)}	$I_{C} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$	_	0.1	0.25	V
Transition frequency	f _T	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 1 \text{ mA}$	60		_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	0.95		pF

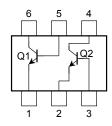
Note: hFE Classification Y (F): 120 ~ 140, GR (H): 200 ~ 400

() Marking symbol

Marking

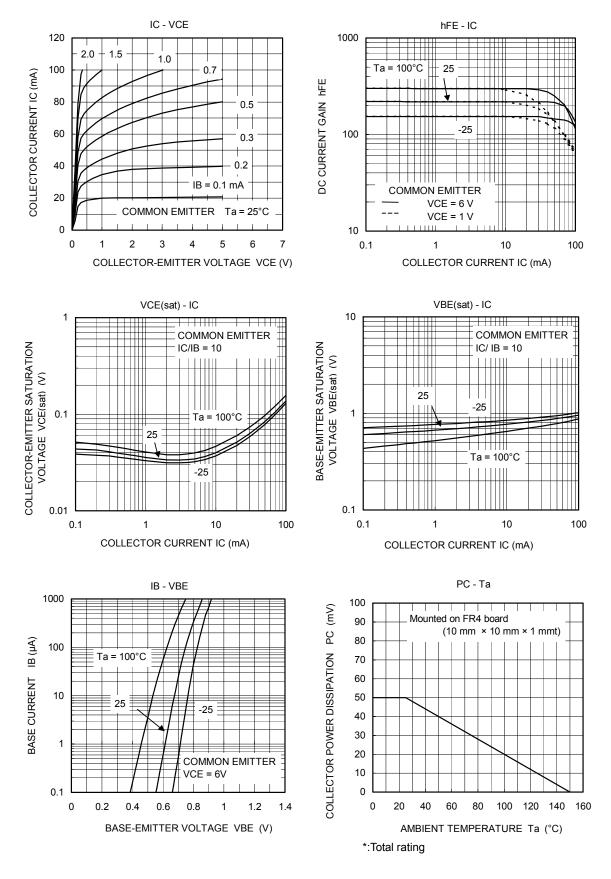


Equivalent Circuit (top view)



<u>TOSHIBA</u>

Q1, Q2 Common



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